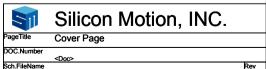
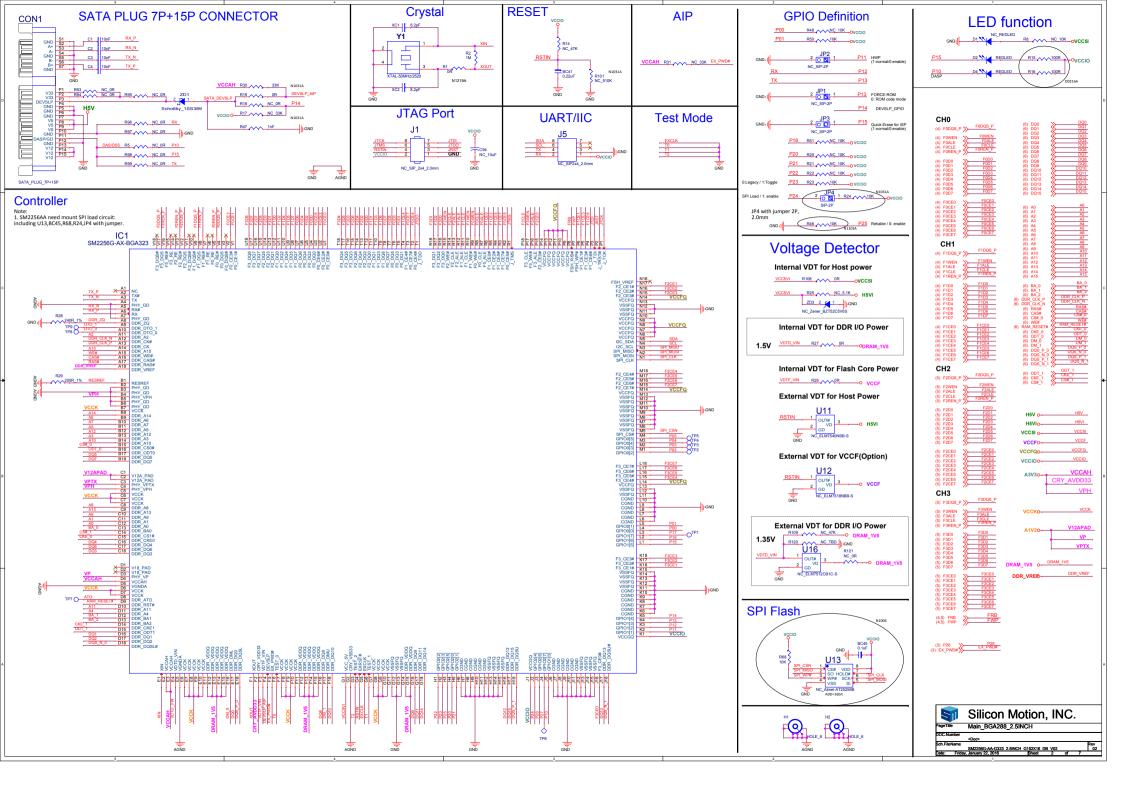
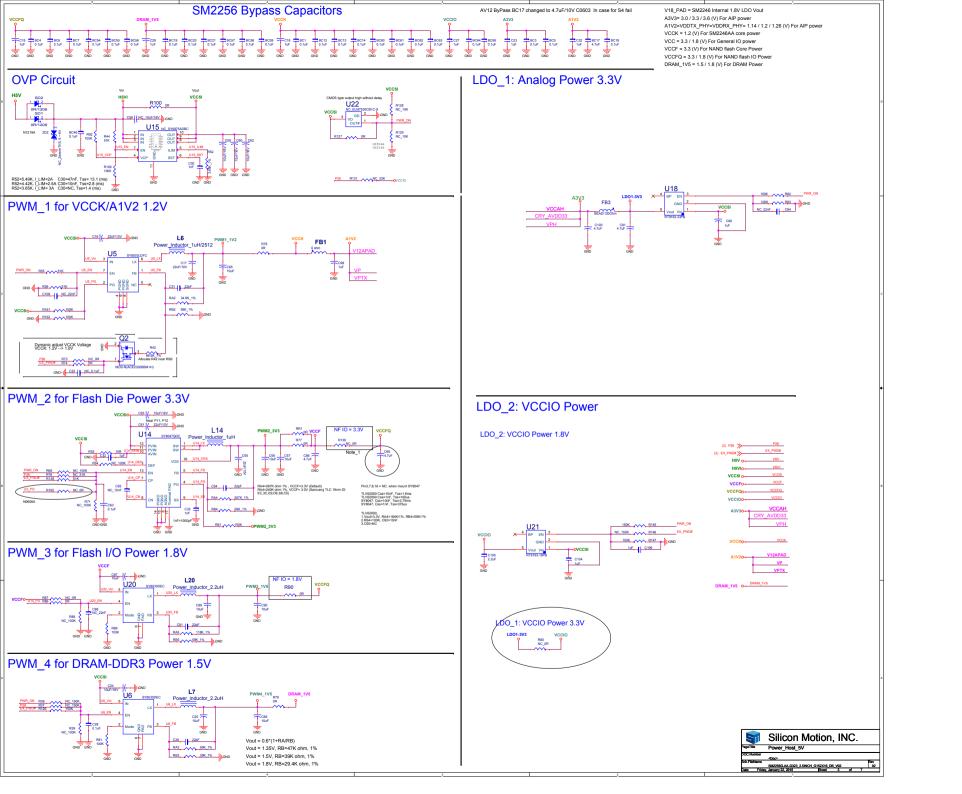
Revision History

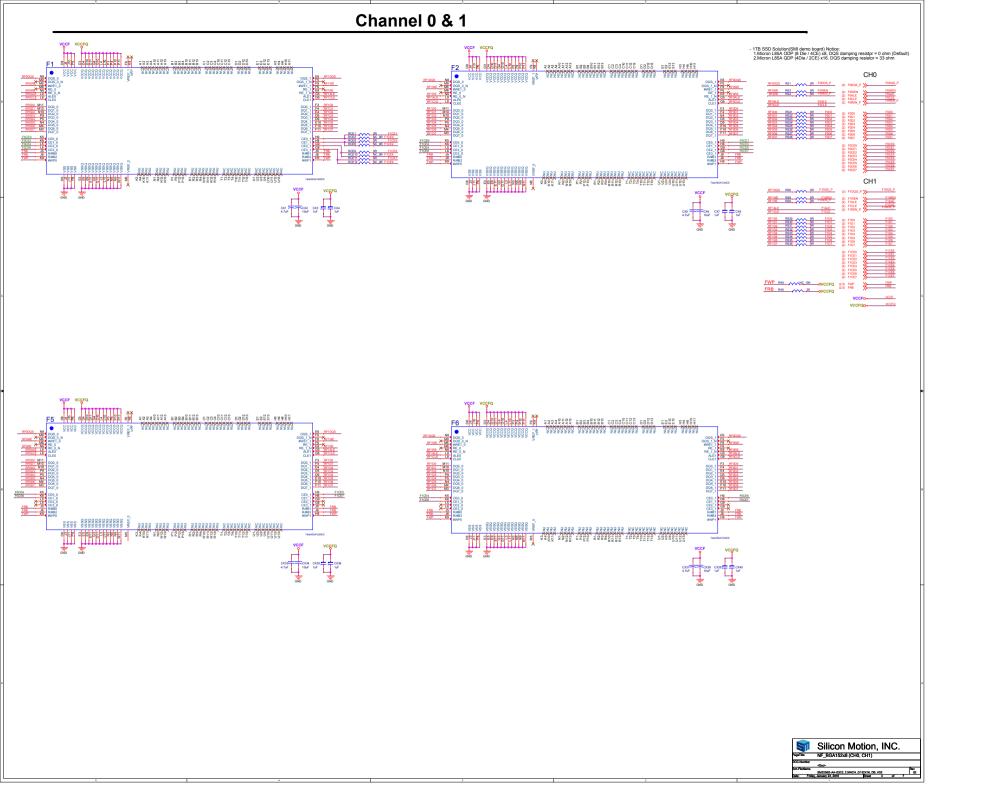
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Reason for redrawing	Page Update	Drawed	Checked	Approved
Preliminary		Brian Lee	Austin Lin	Barry Chang
First Time Release 1.For reduce power circuit, change U5 from SY8047 to SY8003L. And delete DEVSLP option circuit. 2.Confirm device sleep mode power circuit 2.1VCCK equal to 0.98V, Turn off VCCF, VCCFQ and DRAM power at device sleep mode. 2.2 A3V3 and GPIO power doesn't turn off at device sleep mode	3	Austin Lin	Brian Lee	Barry Chang
BOM modify. Add SPI EEROM circuit. Change below parts from NC to mounting. 1.U13 (25AA256-I/SN), R68 (10 ohm/0402), BC45 (0.1uF/0402)	2	Brian Lee	Austin Lin	Barry Chang
1. Update BOM Sheet _1: FSH=16, SPI, BOM list with SPI EEPROM. (for enable SPI load 1.1 Change R24 from NC to 10K ohm, 0402. 1.2 Change JP4 from NC to SIP, 2P, 2.0mm with jumper (2P, 2.0mm) 2. 2 sheet BOM update. 2.1 Change R15,R16 from 10K ohm, 0402 to 2K ohm, 0402. 2.2 Change R30 from 10K ohm, 0402 to 33K ohm, 0402. 2.3 Change R30 from 10K ohm, 0402 to 33K ohm, 0402. 2.3 Change R101 from NC to 510K ohm, 0402	2	Brian Lee	Austin Lin	Barry Chang
BOM modify. For enable NAND reliable mode setting. Change R46 from NC to 10K ohm, 0402.	2	Brian Lee	Austin Lin	Barry Chang
1. For Samsung TLC 19nm (ID: EC,3C,E9,DE,88,C5): setting VCCF=VCCFQ=3.0V (RA4=240K, O402, 1%) 2. Modify power control circuit: 2.1 Change U22 from VDT 4V to NC 2.2 Change R127 from NC to 0 ohm, 0402.	3	Brian Lee	Austin Lin	Barry Chang
1.Modify power circuit BOM for cost down. Change SD1 from SCHOTTKY_SS2040/2A to resistor 0 ohm/1206. 2.For fine tune crystal signal quality, modify R1 from resistor 100 ohm_1%/0402 to 0 ohm/0402.	3	Brian Lee	Austin Lin	Barry Chang
1.Modify power circuit BOM. 1.1 Change U22 from 4V VDT to 3V VDT. 1.2 Change R127 from 0R to NC. 1.3 Change R52 from 5.49K 1% to 3.65K 1%. I_limit increase from 2A to 3A.	3	Brian Lee	Austin Lin	Barry Chang
For SM2256-AB BOM 1.Adjust LED brightness Change R15,R16 resistor value from 2K ohm to 100 ohm (0402) 2.Change GPIO VCC voltage from 3.3V to 1.8V 2.1 Change U21 from NC to LD0 ELM88181BAS(SOT-23) 2.2 Change R80 from resistor 0 ohm to NC.(0603) 3.SPI EEROM circuit remove BOM option.	2,3	Brian Lee	Austin Lin	Barry Chang
Modify power control circuit BOM, for FW control NAND data protection flow, 1.1 Change U22 from VDT 3V to NC 1.2 Change R127 from NC to 0 ohm, 0402.	2	Brian Lee	Austin Lin	Barry Chang

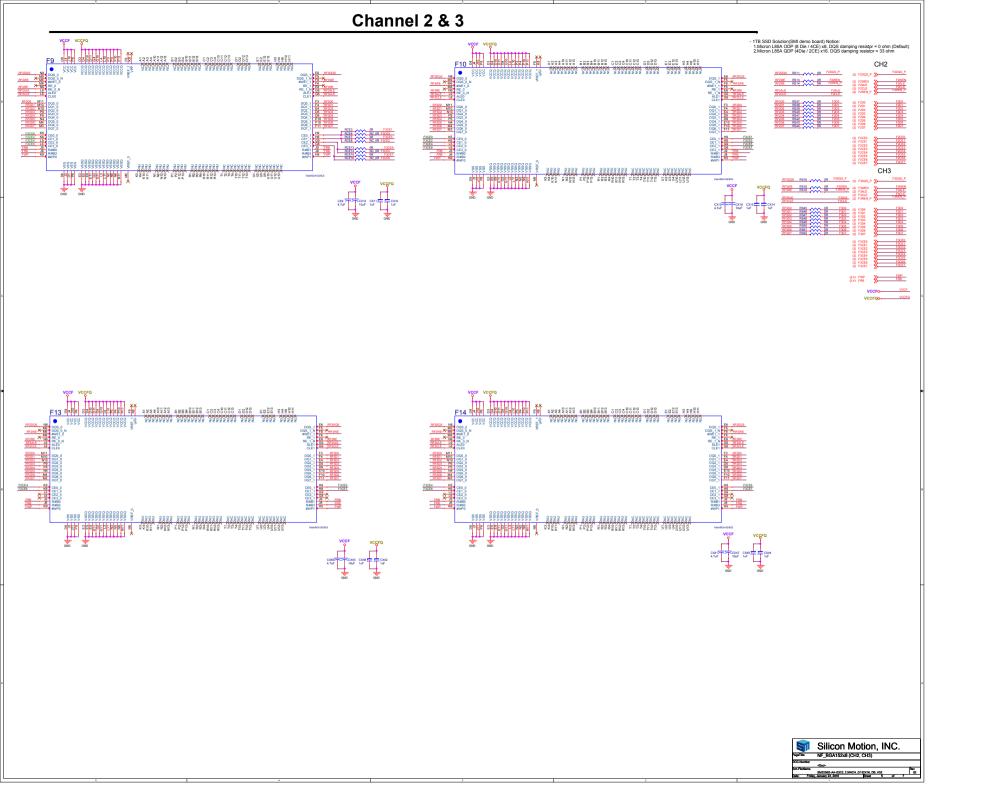
Page1	Cover_Page
Page2	Controller_BGA323_2.5INCH
Page3	Power_Host_5V
Page4	NF_BGA152x8 (CH0, CH1)
Page5	NF_BGA152x8 (CH2, CH3)
Page6	DRAM_DDR3-16x2
Page7	Flash Mounting Guide

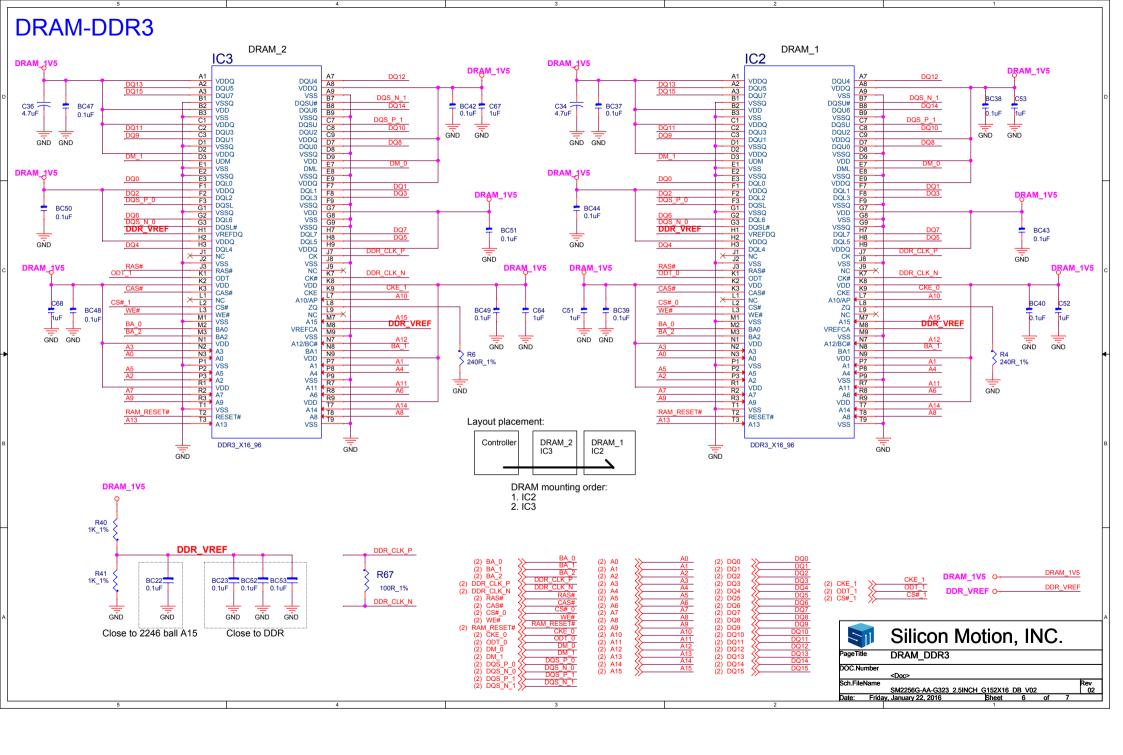


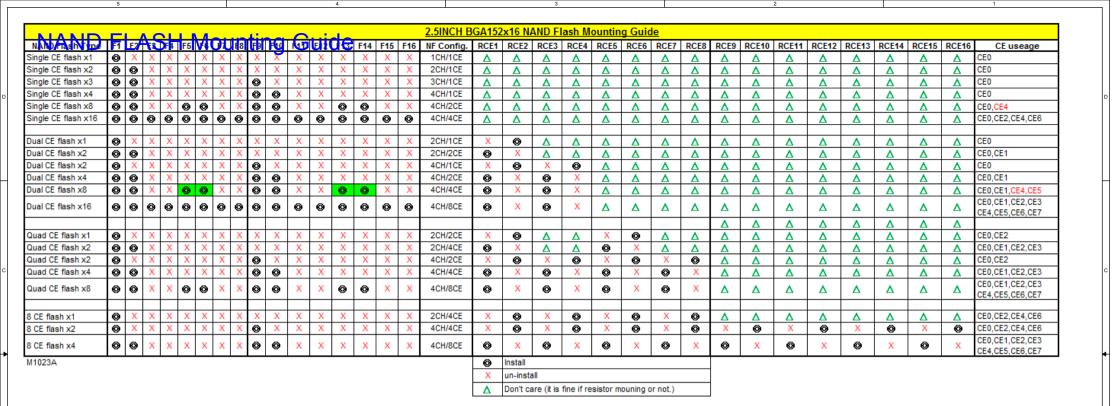








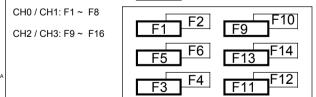






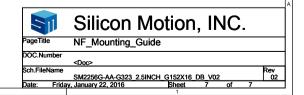
BOT

F8



F7

TOP



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